

MS23P09

P-Channel 20-V (D-S) MOSFET

Description

The MS23P09 is using trench DMOS technology. This advanced technology has been especially tailored to minimize $R_{DS(ON)}$, provide superior switching performance and commutation mode. These devices are well suited for high efficiency fast switching applications.

The device meets the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced DMOS Trench Technology
- Suit for -1.8V Gate Drive Applications
- Improve dv/dt Capability
- Fast Switching
- Green Device Available

Typical Applications

- Battery Protection
- Load Switch
- Hand-held Instrument

Package type : SOT-23

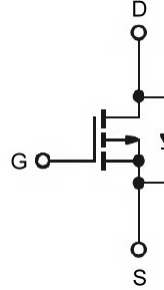
Packing & Order Information

3,000/Reel

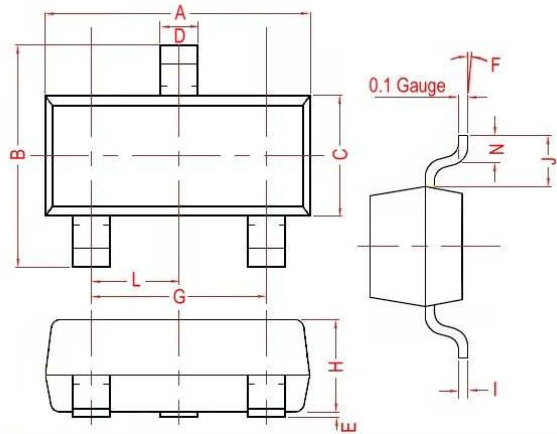


RoHS Compliant

Graphic Symbol

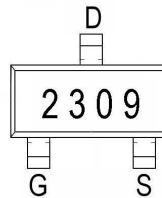


Package Dimension



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90 Ref.	
B	2.30	3.00	H	0.90	1.30
C	1.20	1.75	I	0.05	0.21
D	0.30	0.50	J	0.58 Ref.	
E	0.01	0.15	L	0.95 Typ.	
F	0°	10°	N	0.20 Min.	

Marking



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 10	V
I_D	Continuous Drain Current ($T_C = 25^\circ\text{C}$)	-5.8	A
	Continuous Drain Current ($T_C = 100^\circ\text{C}$)	-3.7	A
I_{DM}	Pulsed Drain Current ^{1,2} ($T_C = 25^\circ\text{C}$)	-23	A
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	1.56	W
T_J/T_{STG}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$

Thermal Resistance Ratings

Symbol	Parameter	Maximum	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ³	80	$^\circ\text{C/W}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-0.3	-0.6	-1.0	V
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-20	-	-	V
g_{fs}	Forward Transconductance	$V_{DS} = -10\text{V}, I_D = -3\text{A}$	-	8.4	-	S
I_{GSS}	Gate-Source Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 10\text{V}$	-	-	± 100	nA
I_{DSS}	Drain-Source Leakage Current	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	-	-	-1	μA
		$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$	-	-	-10	μA
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS} = -4.5\text{V}, I_D = -4\text{A}$	-	28	33	m Ω
		$V_{GS} = -2.5\text{V}, I_D = -3\text{A}$	-	37	45	
		$V_{GS} = -1.8\text{V}, I_D = -2\text{A}$	-	49	65	
V_{SD}	Diode Forward Voltage ²	$I_S = -1\text{A}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	-	-	-1.0	V
I_S	Continuous Source Current (Diode)	$V_G = V_D = 0\text{V}, \text{Force Current}$	-	-	-5.8	A
I_{SM}	Pulsed Source Current (Diode)		-	-	-11.6	

Notes

1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

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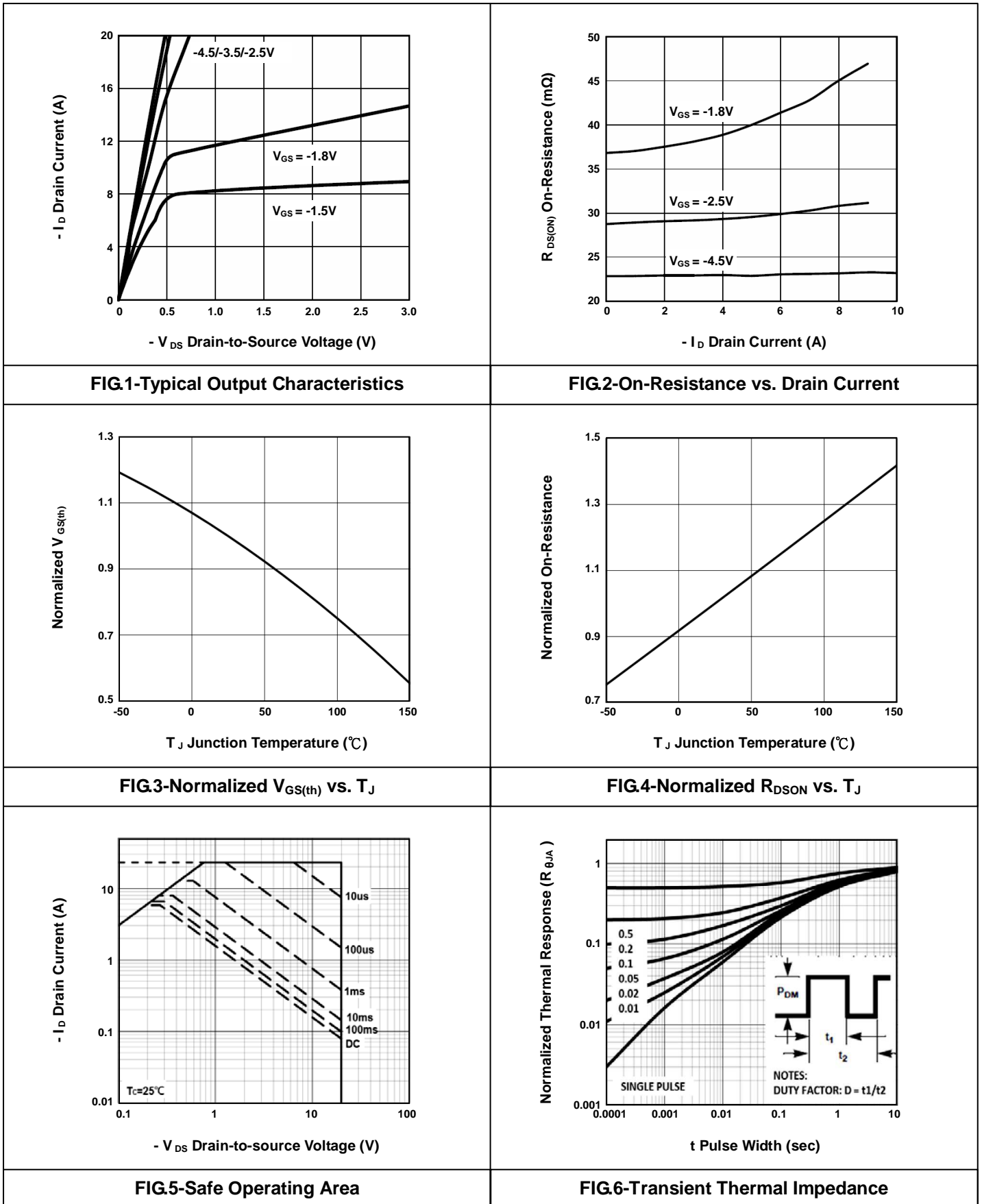
Dynamic and switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Q_g	Total Gate Charge ^{2,3}	$V_{DS} = -10V$	--	16.1	--	nC
Q_{gs}	Gate-Source Charge	$I_D = -4A$	--	1.8	--	
Q_{gd}	Gate-Drain Charge	$V_{GS} = -4.5V$	--	3.8	--	
$t_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DS} = -10V$	--	8.2	--	ns
t_r	Rise Time	$I_D = -1A$	--	30	--	
$t_{d(off)}$	Turn-Off Delay Time	$V_{GS} = -4.5V$	--	71.1	--	
t_f	Fall Time	$R_G = 25\Omega$	--	19.8	--	
C_{ISS}	Input Capacitance	$V_{DS} = -15V$	--	1440	--	pF
C_{OSS}	Output Capacitance	$V_{GS} = 0V$	--	155	--	
C_{RSS}	Reverse Transfer Capacitance	$f = 1.0MHz$	--	115	--	

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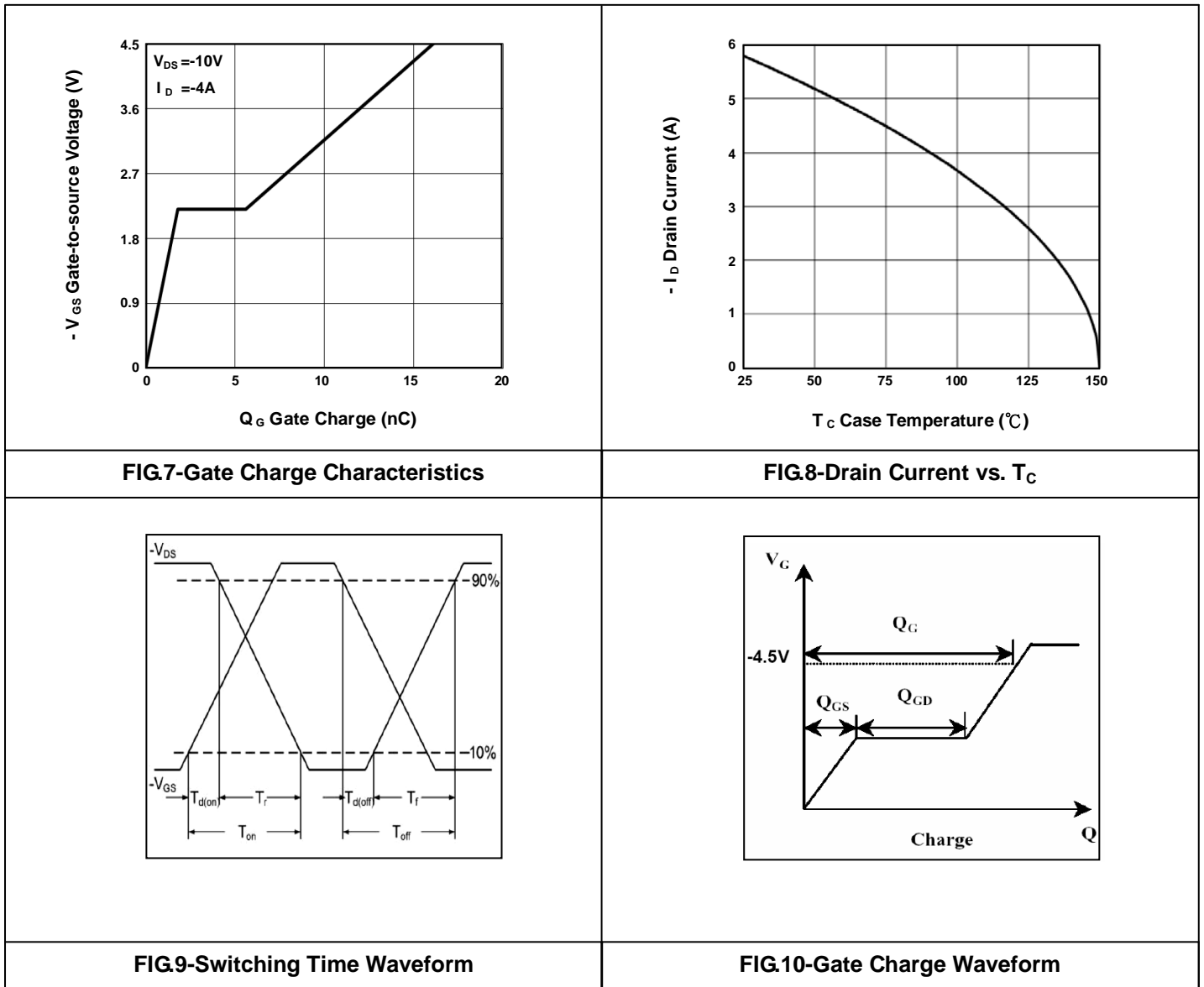
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- Typical Electrical Characteristics



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